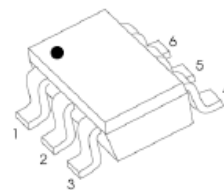


Plastic-Encapsulate Transistors

DUAL TRANSISTOR (PNP+PNP)

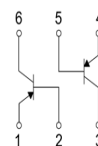
MARKING: 2F



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-600	mA
P_C	Collector Power Dissipation	200	mW
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

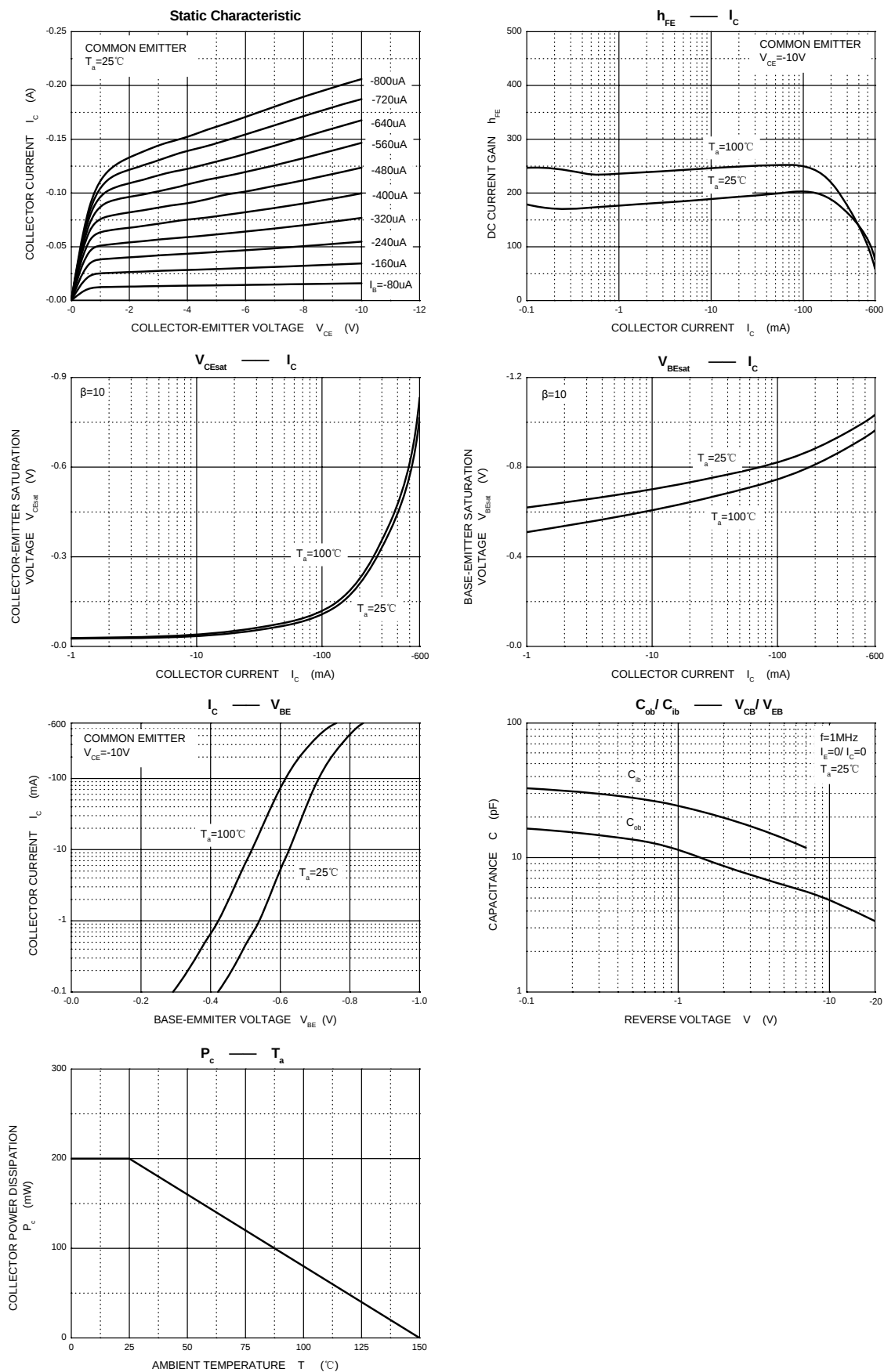
SOT-363



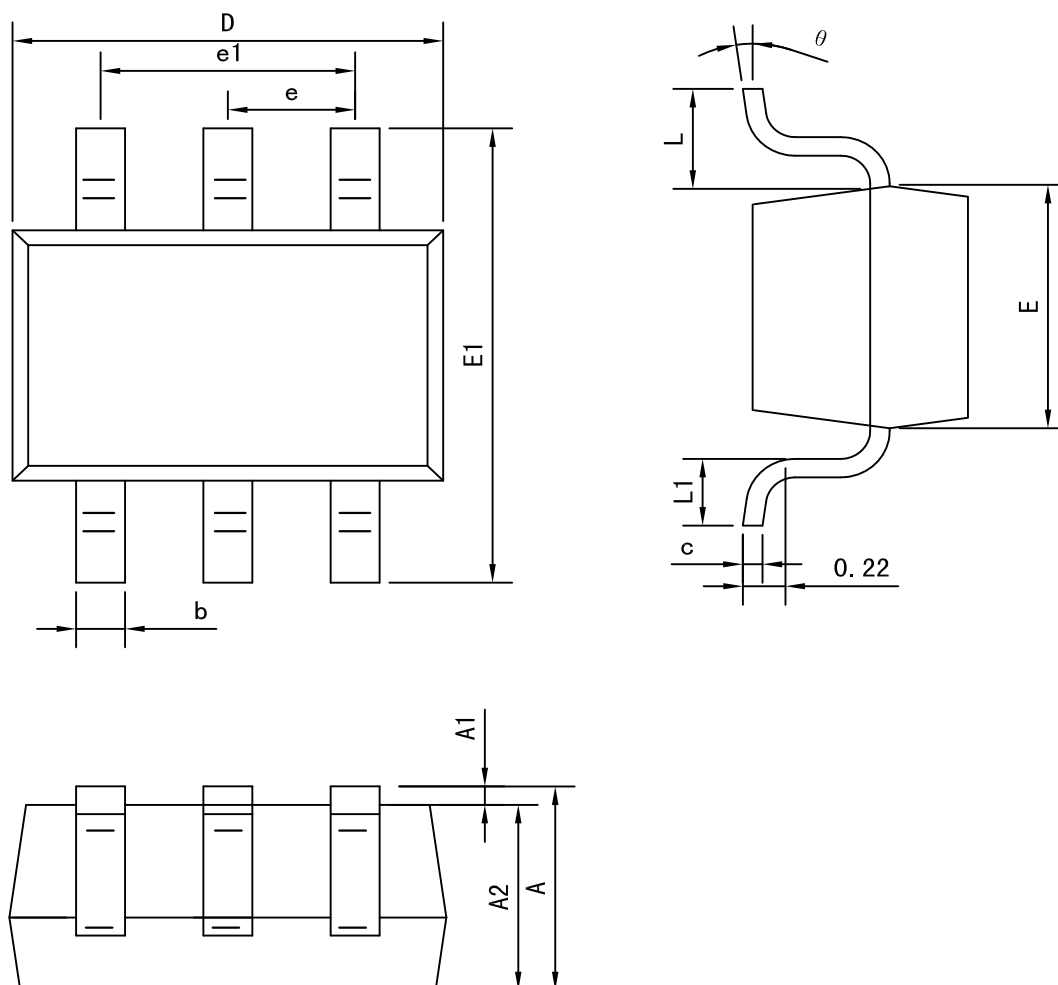
ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu\text{A}$, $I_E = 0$	-60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10\text{mA}$, $I_B = 0$	-60		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}$, $I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -50\text{V}$, $I_E = 0$		-10	nA
Collector cut-off current	I_{CEX}	$V_{CE} = -30\text{V}$, $V_{EB(off)} = -0.5\text{V}$		-50	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}$, $I_C = 0$		-10	nA
DC current gain	$h_{FE(1)}$	$V_{CE} = -10\text{V}$, $I_C = -0.1\text{mA}$	75		
	$h_{FE(2)}$	$V_{CE} = -10\text{V}$, $I_C = -1\text{mA}$	100		
	$h_{FE(3)}$	$V_{CE} = -10\text{V}$, $I_C = -10\text{mA}$	100		
	$h_{FE(4)}$	$V_{CE} = -10\text{V}$, $I_C = -150\text{mA}$	100	300	
	$h_{FE(5)}$	$V_{CE} = -10\text{V}$, $I_C = -500\text{mA}$	50		
Collector-emitter saturation voltage	$V_{CE(sat)1}$	$I_C = -150\text{mA}$, $I_B = -15\text{mA}$		-0.4	V
	$V_{CE(sat)2}$	$I_C = -500\text{mA}$, $I_B = -50\text{mA}$		-1.6	V
Base-emitter saturation voltage	$V_{BE(sat)1}$	$I_C = -150\text{mA}$, $I_B = -15\text{mA}$		-1.3	V
	$V_{BE(sat)2}$	$I_C = -500\text{mA}$, $I_B = -50\text{mA}$		-2.6	V
Transition frequency	f_T	$V_{CE} = -20\text{V}$, $I_C = -50\text{mA}$, $f = 100\text{MHz}$	200		MHz
Output Capacitance	C_{ob}	$V_{CB} = -10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$		8	pF
Input Capacitance	C_{ib}	$V_{EB} = -2\text{V}$, $I_C = 0$, $f = 1\text{MHz}$		30	pF
Delay time	t_d	$V_{CC} = -30\text{V}$, $I_C = -150\text{mA}$, $I_{B1} = -15\text{mA}$		10	nS
Rise time	t_r			40	nS
Storage time	t_s	$V_{CC} = -6\text{V}$, $I_C = -150\text{mA}$,		225	nS
Fall time	t_f	$I_{B1} = I_{B2} = -15\text{mA}$		60	nS

Typical Characteristics



SOT-363 Package outline dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.150	0.350
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP	
e1	1.200	1.400
L	0.525 REF	
L1	0.260	0.460
θ	0°	8°